

TO-252 N Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管

■Features 特点

Low on-resistance 低导通电阻

$R_{DS(ON)}=34m\Omega(\text{Type})@V_{GS}=10V$

$R_{DS(ON)}=36m\Omega(\text{Type})@V_{GS}=4.5V$

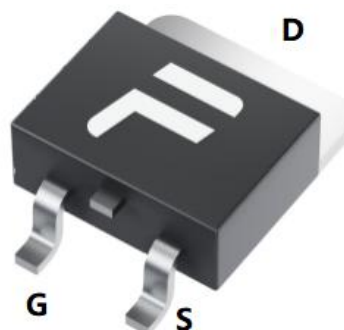
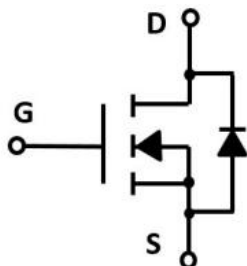
■Applications 应用

Backlight Drive 背光驱动

DC-DC Conversion 升压转换

Power Management 电源管理

■Internal Schematic Diagram 内部结构



■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	60	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 20	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_C = 25^\circ\text{C}$ at $T_C = 100^\circ\text{C}$)	20 12	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	60	A
Total Device Dissipation 总耗散功率	P_{TOT} (at $T_C = 25^\circ\text{C}$ at $T_C = 100^\circ\text{C}$)	28 11	W
Thermal Resistance Junction-Case 热阻	$R_{\theta JC}$	4.4	$^\circ\text{C}/\text{W}$
Avalanche Energy Single Pulse 雪崩能量	E_{AS}	30	mJ
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ\text{C}$

Electrical Characteristics 电特性

 (T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D =250uA, V _{GS} =0V)	BV _{DSS}	60	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D =250uA, V _{GS} =V _{DS})	V _{GS(th)}	1.0	1.5	2.5	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} =60V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 栅极漏电流(V _{GS} =±20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D =20A, V _{GS} =10V) (I _D =10A, V _{GS} =4.5V)	R _{DS(ON)}	—	34 36	43 47	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} =10A, V _{GS} =0V)	V _{SD}	—	0.8	1.2	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} =30V, f=1MHz)	C _{ISS}	—	1018	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} =30V, f=1MHz)	C _{OSS}	—	70	—	pF
Reverse Transfer Capacitance 反馈电容(V _{GS} =0V, V _{DS} =30V, f=1MHz)	C _{RSS}	—	62	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} =30V, I _D =10A, V _{GS} =10V)	Q _g	—	26	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} =30V, I _D =10A, V _{GS} =10V)	Q _{gs}	—	5.4	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} =30V, I _D =10A, V _{GS} =10V)	Q _{gd}	—	6.5	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} =30V I _D =2A, R _{GEN} =3Ω, V _{GS} =10V)	t _{d(on)}	—	10	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} =30V I _D =2A, R _{GEN} =3Ω, V _{GS} =10V)	t _r	—	20	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} =30V I _D =2A, R _{GEN} =3Ω, V _{GS} =10V)	t _{d(off)}	—	29	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} =30V I _D =2A, R _{GEN} =3Ω, V _{GS} =10V)	t _f	—	22	—	ns

■ Typical Characteristic Curve 典型特性曲线

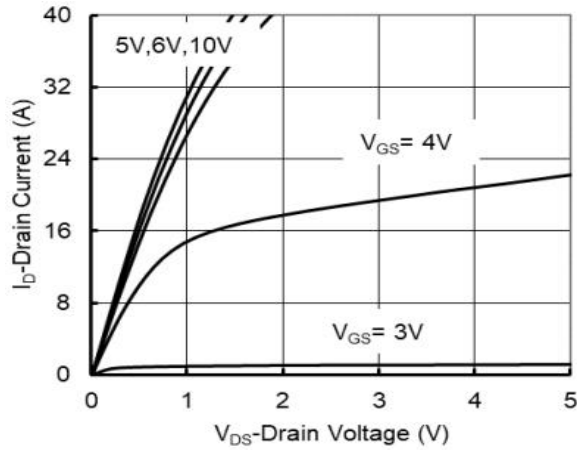


Figure 1: Output Characteristics

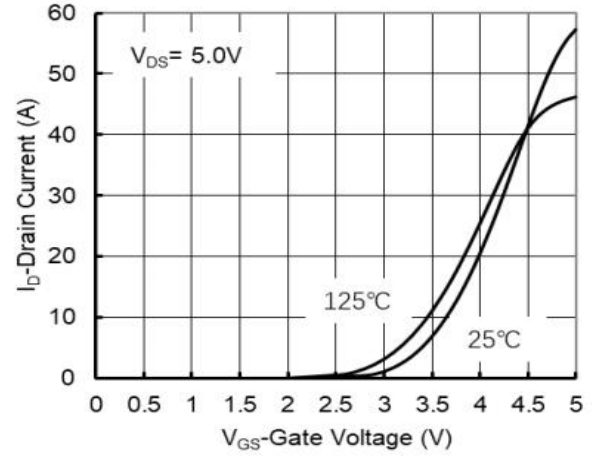


Figure 2: Transfer Characteristics

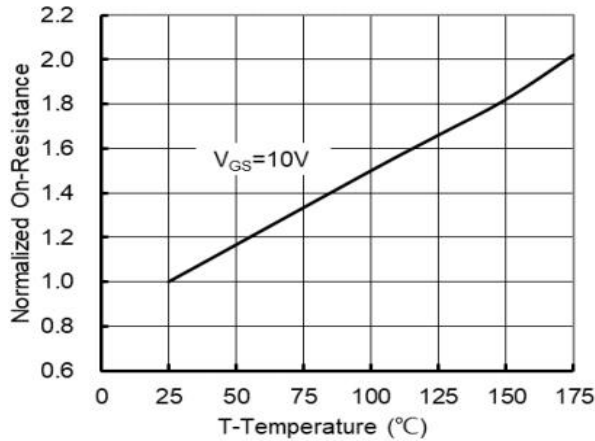


Figure 3: On-Resistance vs. T_J

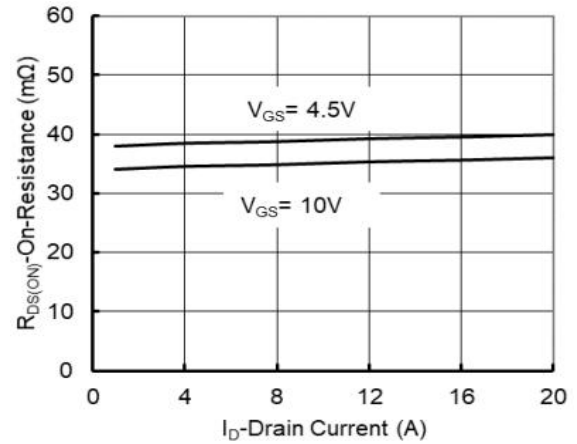


Figure 4: On-Resistance vs. Drain Current

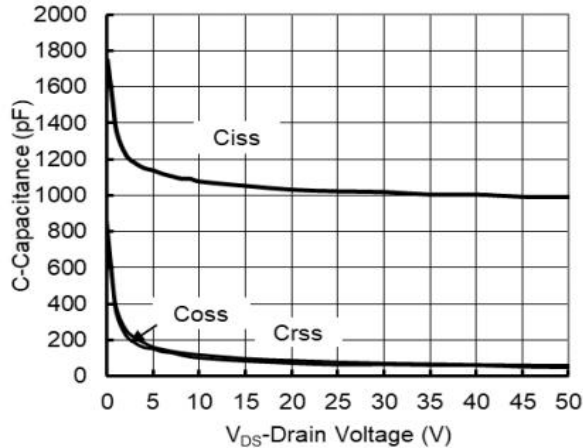


Figure 5: Capacitance Characteristics

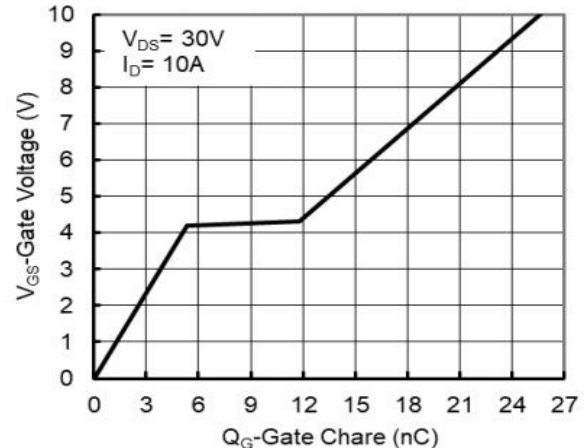


Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线

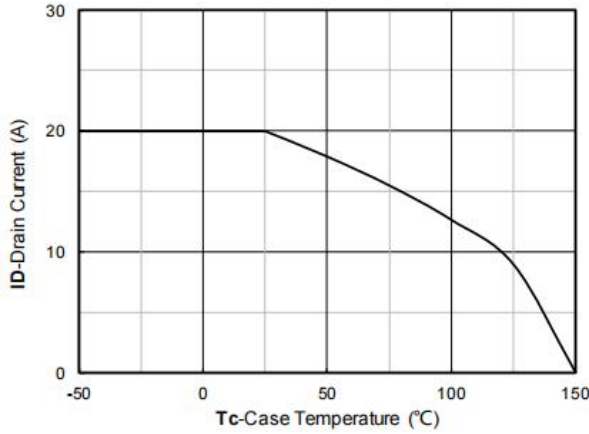


Figure 7: Drain Current Characteristics

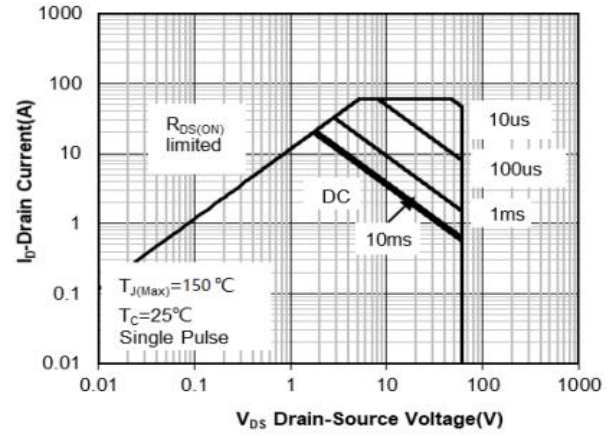


Figure 8: Safe Operating Area

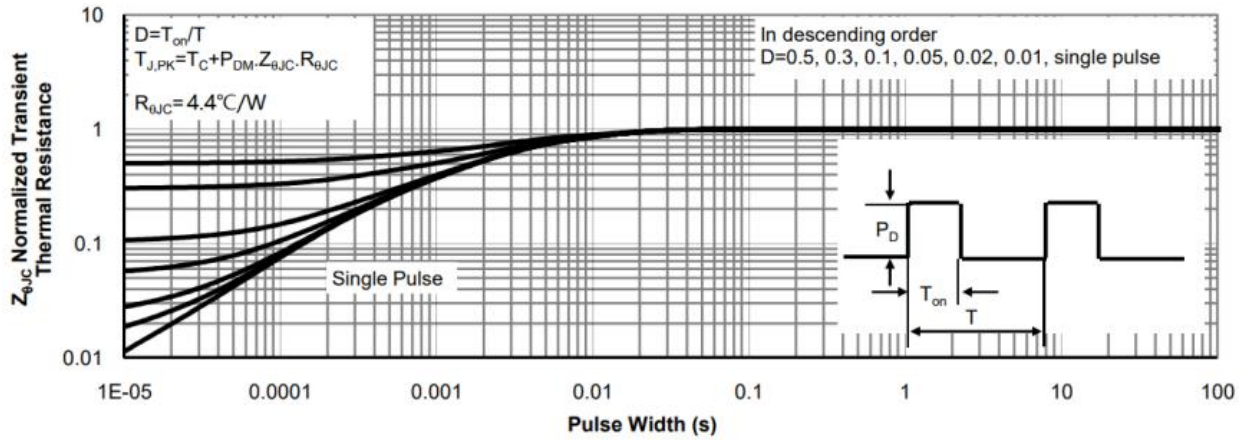
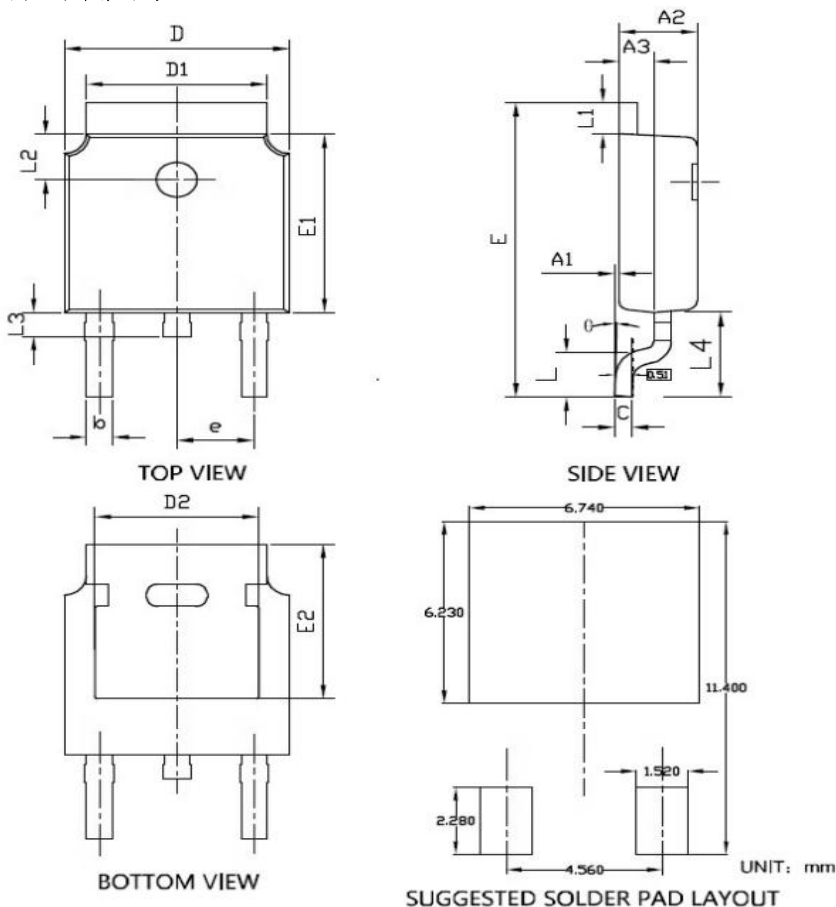


Figure 9: Transient Thermal Response Curve

Dimension 外形封装尺寸



DIMENSIONS						
SYMBOL	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.008	0.000	---	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.023	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.189	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	---	0.050	0.900	---	1.270
L2	0.055	---	0.075	1.400	---	1.900
L3	0.240	0.310	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
Ø	0°	---	10°	0°	---	10°